TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH574FK

#### Octal D-Type Flip-Flop with 3-State Output

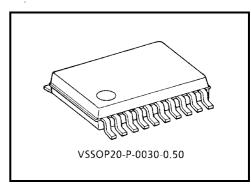
The TC7MH574FK is an advanced high speed CMOS octal flip-flop with 3-state output fabricated with silicon gate  $\rm C^2MOS$  technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

This 8 bit D-type flip-flop is controlled by a clock input (CK) and an output enable input  $(\overline{OE})$ .

When the  $\overline{\text{OE}}$  input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

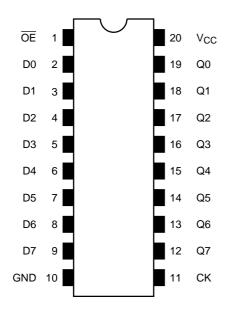


Weight: 0.03 g (typ.)

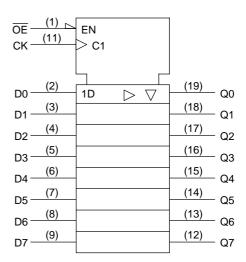
#### **Features**

- High speed:  $f_{max} = 180 \text{ MHz}$  (typ.) (VCC = 5 V)
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: t<sub>p</sub>LH ≈ t<sub>p</sub>HL
- Wide operating voltage range:  $V_{CC \text{ (opr)}} = 2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS574

### Pin Assignment (top view)



#### **IEC Logic Symbol**



#### **Truth Table**

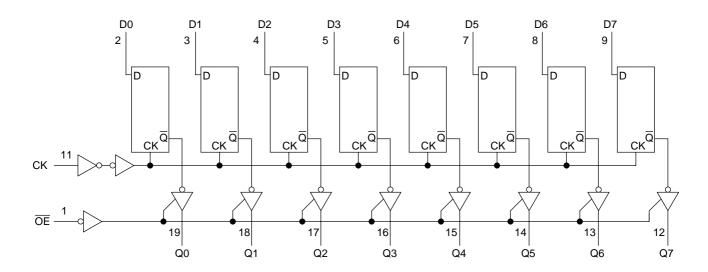
	Outputs		
ŌĒ	CK	D	Outputs
Н	X	Х	Z
L	7_	Х	Q <sub>n</sub>
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q<sub>n</sub>: No change

#### **System Diagram**



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## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	P <sub>D</sub>	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V
Input lise and fail tille	αι/uv	$0 \sim 20 \; (V_{CC} = 5 \pm 0.5 \; V)$	113/ V

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol Test Condition			-	Ta = 25°C		Ta = -40~85°C		Unit	
Charac	Rensuos	Symbol			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
					2.0	1.50	_		1.50		
Input voltage	High level	V <sub>IH</sub>		_		V <sub>CC</sub> × 0.7			V <sub>CC</sub> × 0.7		V
Imput voltage					2.0		_	0.50	_	0.50	v
	Low level	$V_{IL}$		_	3.0~5.5		_	$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$	_	$\begin{array}{c} V_{CC} \\ \times  0.3 \end{array}$	
					2.0	1.9	2.0	_	1.9	_	
				$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		
	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub>		4.5	4.4	4.5		4.4		
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_		2.48		
Output				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_		3.80	1	V
voltage		V <sub>OL</sub>		I <sub>OL</sub> = 50 μA	2.0		0	0.1	_	0.1	
					3.0		0	0.1	_	0.1	
	Low level		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0		_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$			_	0.36	_	0.44	
3-state output	off-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25		±2.50	μА
Input leakage	current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 \	/ or GND	0~5.5		_	±0.1	_	±1.0	μΑ
Quiescent sup	ply current	Icc	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	4.0	_	40.0	μΑ

## Timing Requirements (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	/mbol Test Condition		Ta = 25°C		Ta = -40~85°C	Unit	
Characteristics			V <sub>CC</sub> (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	t <sub>w (H)</sub>		$3.3 \pm 0.3$	_	5.0	5.0	ns	
(CK)	t <sub>w (L)</sub>	_	$5.0 \pm 0.5$	_	5.0	5.0	115	
Minimum set-up time	ts		$3.3 \pm 0.3$	_	3.5	3.5	ns	
		_	$5.0 \pm 0.5$	_	3.5	3.5	115	
Minimum hold time	t <sub>h</sub>		$3.3 \pm 0.3$	_	1.5	1.5	ns	
			$5.0 \pm 0.5$	_	1.5	1.5	115	

#### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	8.5	13.2	1.0	15.5	ns
Propagation delay time	t <sub>pLH</sub>		3.3 ± 0.3	50	_	11.0	16.7	1.0	19.0	
(CK-Q)	t <sub>pHL</sub>	_	5.0 ± 0.5	15	_	5.6	8.6	1.0	10.0	115
			5.0 ± 0.5	50	_	7.1	10.6	1.0	12.0	
			$3.3 \pm 0.3$	15	_	8.2	12.8	1.0	15.0	
2 atata autaut anabla tima	t <sub>pZL</sub>	B. 110	3.3 ± 0.3	50	_	10.7	16.3	1.0	18.5	no
3-state output enable time	t <sub>pZH</sub>	$R_L = 1 \text{ k}\Omega$	5.0 ± 0.5	15	_	5.9	9.0	1.0	10.5	ns
			5.0 ± 0.5	50	_	7.4	11.0	1.0	12.5	
3-state output disable time	t <sub>pLZ</sub>	$R_L = 1 \text{ k}\Omega$	$3.3 \pm 0.3$	50	_	11.0	15.0	1.0	17.0	ns
5-State output disable time	t <sub>pHZ</sub>		$5.0 \pm 0.5$	50	_	7.1	10.1	1.0	11.5	
	f <sub>max</sub>	_	3.3 ± 0.3	15	80	125	_	65	_	- MHz
Maximum clock frequency				50	50	75	_	45	_	
Maximum clock frequency			50.05	15	130	180	_	110	_	
			5.0 ± 0.5	50	85	115	_	75	_	
Output to output skew	t <sub>osLH</sub>	(Note1)	$3.3 \pm 0.3$	50	_	_	1.5	_	1.5	no
Output to output skew	t <sub>osHL</sub>	(Note1)	$5.0 \pm 0.5$	50	_	_	1.0	_	1.0	ns
Input capacitance	C <sub>IN</sub>	-	_		_	4	10	_	10	pF
Output capacitance	C <sub>OUT</sub>	-	_		_	6		_	_	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note2)	_	28		_	_	pF

Note1: This parameter is guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{PLHm}} - t_{\text{PLHn}}|, \, t_{\text{OSHL}} = |t_{\text{PHLm}} - t_{\text{PHLn}}|$ 

Note2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$ 

And the total C<sub>PD</sub> when n pcs of latch operate can be gained by the following equation:

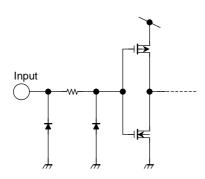
 $C_{PD}$  (total) = 20 + 8 · n

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## Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

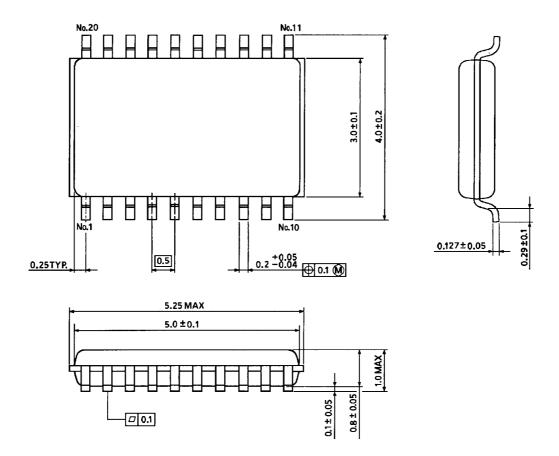
Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
Granacieristics	Symbol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	8.0	1.0	V
Quiet output minimum dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.8	-1.0	V
Minimum high level dynamic input voltage $V_{\mathrm{IH}}$	$V_{IHD}$	C <sub>L</sub> = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage $V_{\rm IL}$	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	1.5	V

## Input Equivalent Circuit



### **Package Dimensions**

**TOSHIBA** 



Weight: 0.03 g (typ.)

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